

EAST - [10801739.wsp:1]

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Drafts
 BRS: bipolar near transistor and ((variable select\$2) near (breakdown near voltage))
 Pending
 Active
 L1: (0) bipolar near transistor and (variable near (breakdown near voltage))
 L2: (60) bipolar near transistor and ((variable select\$2) near (breakdown near voltage))
 L3: (0) bipolar near transistor and ((variable (select\$2 near value)) near (breakdown near voltage))
 L4: (9) 2 and (emitter and sinker and collector)
 L5: (9) 2 and (emitter and base and sinker and collector)
 L6: (9) 2 and emitter and base and sinker and collector
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 DBs US-PGPUB: USPAT: USOCR: Plurals
 Default operator: OR Highlight all hit terms initially

bipolar near transistor and ((variable select\$2) near (breakdown near voltage))

BRS form IS&R form Image Text HTML

| | U | 1 | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|--------------------------|--------------------------|-------------------|------------|-------|---|------------|---|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20050078848 A1 | 20050414 | 32 | Power amplifier and method for split voice coil transducer or speaker | 381/401 | 381/400; 381/402 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20040164346 A1 | 20040826 | 7 | Power switching transistor with low drain to gate capacitance | 257/328 | 257/E29.257 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 20040108547 A1 | 20040610 | 6 | Power switching transistor with low drain to gate capacitance | 257/335 | 257/E29.257 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 20040009643 A1 | 20040115 | 15 | METHOD FOR FABRICATING A HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED CO | 438/268 | 257/328; 257/E21.418; 257/E29.257 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030155980 A1 | 20030821 | 6 | Semiconductor device including semiconductor element of high breakdown voltage | 330/311 | |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030128014 A1 | 20030710 | 9 | Alternator for a motor vehicle with energising information output | 322/28 | |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030068863 A1 | 20030410 | 13 | Method for fabricating a power semiconductor device having a floating island voltage sustaining layer | 438/268 | 257/E21.418; 257/E29.013; 257/E29.257 |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030057480 A1 | 20030327 | 8 | Voltage-controlled vertical bidirectional monolithic switch | 257/328 | 257/E29.215 |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030038680 A1 | 20030227 | 9 | RF amplifier and method therefor | 330/298 | |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030038340 A1 | 20030227 | 17 | Low-voltage punch-through bi-directional transient-voltage suppression devices and methods of making the same | 257/546 | 257/E21.361; 257/E29.332 |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020175391 A1 | 20021128 | 17 | LOW-VOLTAGE PUNCH-THROUGH BI-DIRECTIONAL TRANSIENT-VOLTAGE SUPPRESSION DEVICES AND METHODS OF MAKING THE SAME | 257/497 | 257/361; 257/362; 257/E21.361 |

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